MLSM
MICROELECTRONICS

MLSBA2301
-20V/-2.3A P-Channel MOSFET

Features

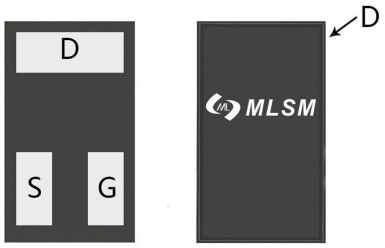
- Leading trench technology for low $R_{DS(on)}$
- Low Gate Charge

Product Summary

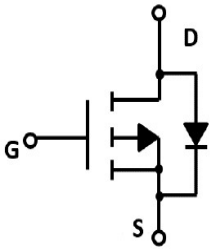
V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-20V	160mΩ@-4.5V	-2.3A
	250mΩ@-2.5V	

Application

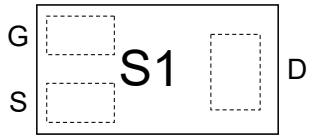
- Video monitor
- Power management



DFN1006-3L view



Schematic diagram



S1: Device code

Marking and pin assignment

Pb-Free RoHS Halogen-Free

Absolute Maximum Ratings (TA=25℃unless otherwise noted)				
Symbol	**Parameter**		**Rating**	**Unit**
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		-20	V
V_{GS}	Gate-Source Voltage		±10	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	Tc=25°C	-2.3	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	Tc=25°C	-8.0	A
I_D	Continuous Drain Current	Tc=25°C	-2.3	A
P_D	Maximum Power Dissipation	Tc=25°C	0.5	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient		178	°C/W

Ordering Information (Example)						
Type	**Package**	**Marking**	**Minimum Package(pcs)**	**Inner Box Quantity(pcs)**	**Outer Carton Quantity(pcs)**	**Delivery Mode**
MLSBA2301	DFN1006-3L	S1	10,000	150,000	600,000	7"reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	**Parameter**	**Condition**	**Min**	**Typ**	**Max**	**Unit**
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V，I_D=-250μA	-20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V，V_{GS}=0V	--	--	-1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±10V，V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}，I_D=-250μA	-0.4	-0.62	-1.0	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=-4.5V，I_D=-2.3A	--	95	160	mΩ
		V_{GS}=-2.5V，I_D=-1.5A	--	140	250	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{ISS}	Input Capacitance	V_{DS}=-10V，V_{GS}=0V， f=1MHz	--	248	--	pF
C_{OSS}	Output Capacitance		--	42	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	31	--	pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS}=-10V，I_D=-2.3A，V_{GS}=-4.5V	--	2.9	--	nC
Q_{gs}	Gate Source Charge		--	0.45	--	nC
Q_{gd}	Gate Drain Charge		--	0.75	--	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=-10V，R_L=5Ω，V_{GS}=-4.5V，R_G=3Ω	--	9.8	--	nS
t_r	Turn-on Rise Time		--	4.9	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	20.5	--	nS
t_f	Turn-Off Fall Time		--	7	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	Tj=25℃，Is=-2.3A	--	--	-1.2	V

Typical Operating Characteristics

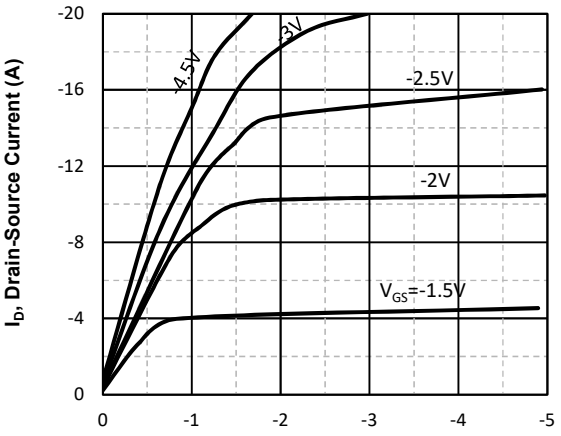


Fig1. Typical Output Characteristics

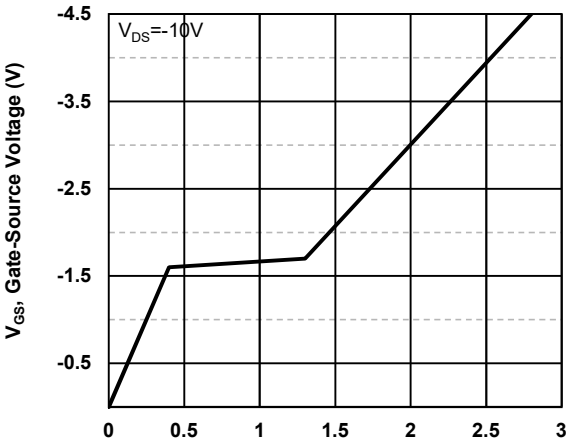


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

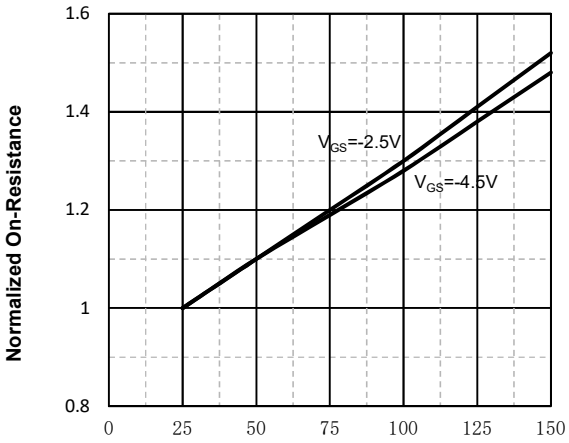


Fig3. Normalized On-Resistance Vs. Temperature

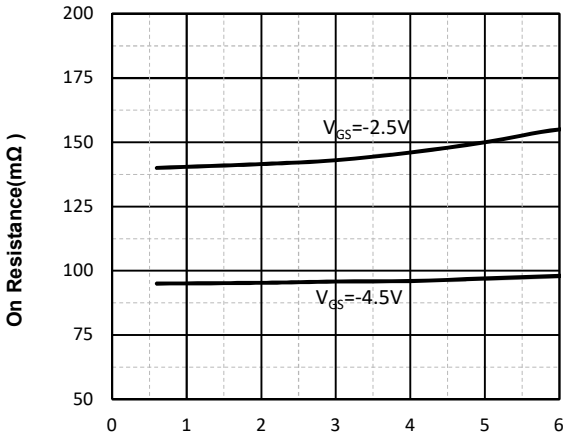


Fig4. On Resistance Vs.Drain-Source Current

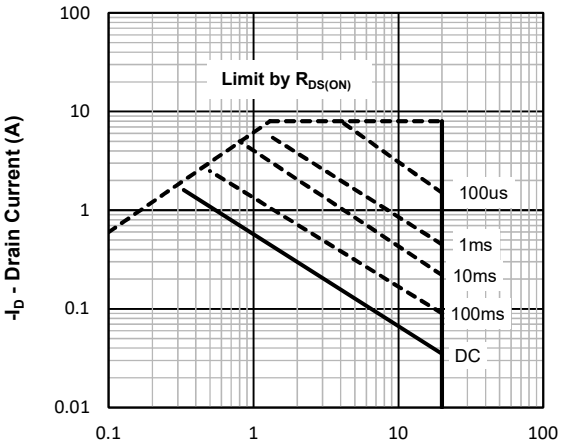


Fig5. Maximum Safe Operating Area

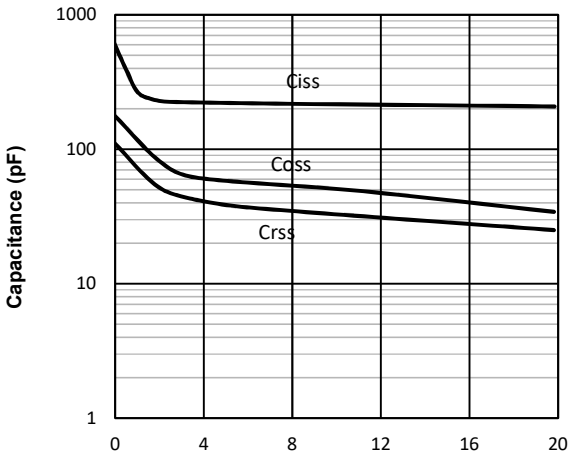
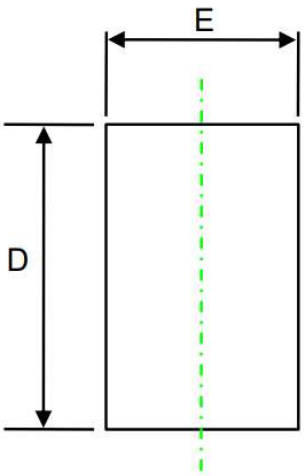
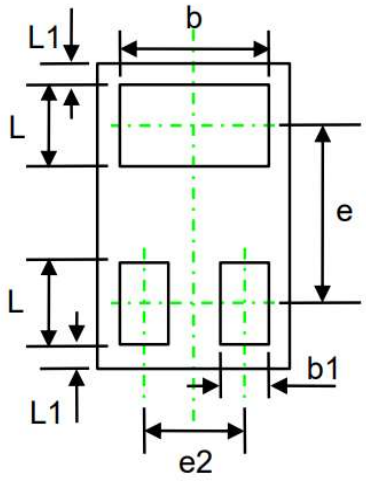


Fig6 Typical Capacitance Vs.Drain-Source Voltage

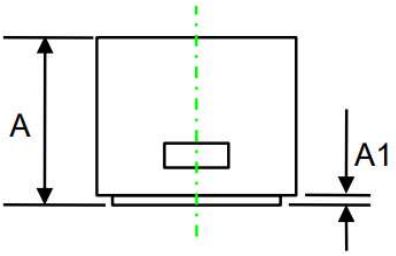
DFN1006-3L Package information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.450	0.550	0.017	0.021
A1	0.000	0.030	0.000	0.001
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.021	0.025
b	0.470	0.550	0.018	0.021
e	0.65TYP		0.025TYP	
e2	0.35TYP		0.013TYP	
L1	0.05TYP		0.001TYP	
L	0.220	0.300	0.008	0.012
b1	0.110	0.190	0.004	0.007